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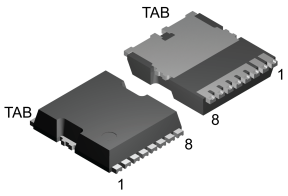
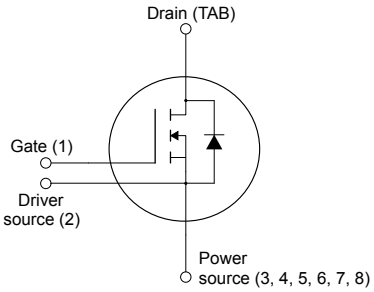
SCT055TO65G3

Datasheet

Silicon carbide Power MOSFET 650 V, 58 mΩ typ., 30 A in a TO-LL package



TO-LL



N-chG1DS2PS34567DTAB

Features

Order code	V_{DS}	$R_{DS(on)}$ typ.	I_D
SCT055TO65G3	650 V	58 mΩ	30 A

- Very fast and robust intrinsic body diode
- Very low $R_{DS(on)}$ over the entire temperature range
- High speed switching performances
- Source sensing pin for increased efficiency

Applications

- Switching mode power supply
- DC-DC converters

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 3rd generation SiC MOSFET technology. The device features a very low $R_{DS(on)}$ over the entire temperature range combined with low capacitances and very high switching operations, which improve application performance in frequency, energy efficiency, system size and weight reduction.

STPOWER

Product status link
SCT055TO65G3

Product summary	
Order code	SCT055TO65G3
Marking	055TO65G3
Package	TO-LL
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operating values)	-5 to 18	
	Gate-source transient voltage, t_p < 1 µs, t ≤ 10 hours over lifetime	-11 to 25	
I_D(1)	Drain current (continuous) at T_C = 25 °C	30	A
	Drain current (continuous) at T_C = 100 °C	30	
I_{DM}(2)	Drain current (pulsed)	147	A
P_{TOT}	Total power dissipation at T_C = 25 °C	234	W
T_{stg}	Storage temperature range	-55 to 175	°C
T_J	Operating junction temperature range		°C

1. *Limited by bonding wires.*
2. *Pulse width is limited by safe operating area.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.64	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	650			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 650 V			10	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = -10 to 22 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 1 mA	1.8	3.0	4.2	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 15 V, I_D = 15 A		67		mΩ
		V_{GS} = 18 V, I_D = 15 A		58	72	
		V_{GS} = 18 V, I_D = 15 A, T_J = 175 °C		75		

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 400 V, f = 1 MHz, V_{GS} = 0 V	-	687	-	pF
C_{oss}	Output capacitance		-	71	-	pF
C_{rss}	Reverse transfer capacitance		-	11	-	pF
Q_g	Total gate charge	V_{DD} = 400 V, V_{GS} = -5 to 18 V, I_D = 15 A	-	31	-	nC
Q_{gs}	Gate-source charge		-	9.5	-	nC
Q_{gd}	Gate-drain charge		-	8.1	-	nC
R_g	Gate input resistance	f = 1 MHz, I_D = 0 A	-	1.6	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	V_{DD} = 400 V, I_D = 15 A, R_G = 8.2 Ω, V_{GS} = -5 V to 18 V	-	42	-	µJ
E_{off}	Turn-off switching energy		-	35.6	-	µJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 400 V, I_D = 15 A, R_G = 8.2 Ω, V_{GS} = -5 to 18 V	-	9.2	-	ns
t_r	Rise time		-	5	-	ns
$t_{d(off)}$	Turn-off delay time		-	19.4	-	ns
t_f	Fall time		-	13.6	-	ns

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}(1)	Continuous diode forward current	T_C = 25 °C	-		30	A
		T_C = 100 °C	-		30	
V_{SD}	Diode forward voltage	I_{SD} = 15 A, V_{GS} = 0 V	-	2.75		V
t_{rr}	Reverse recovery time	I_{SD} = 15 A, 1 kA/µs, V_{DD} = 400 V	-	13		ns
Q_{rr}	Reverse recovery charge		-	57		nC
I_{RRM}	Reverse recovery current		-	7.6		A

1. *Limited by bonding wires.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

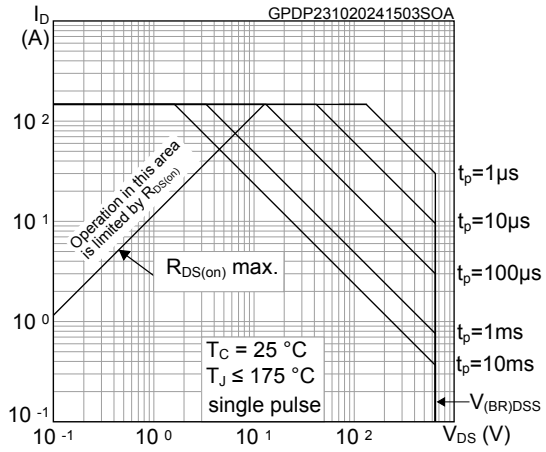


Figure 2. Maximum transient thermal impedance

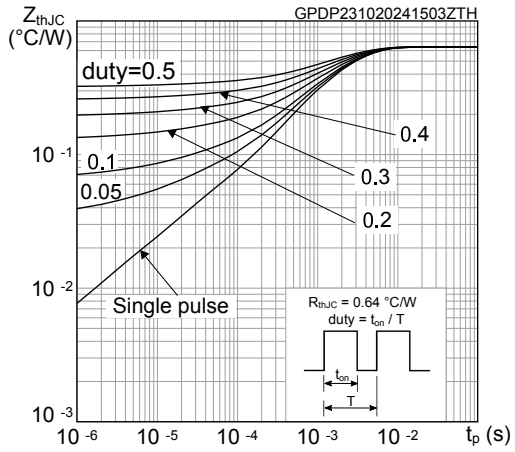


Figure 3. Typical output characteristics (T_J = 25 °C)

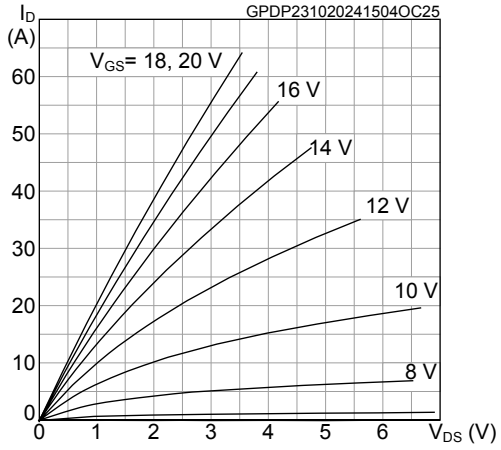


Figure 4. Typical output characteristics (T_J = 175 °C)

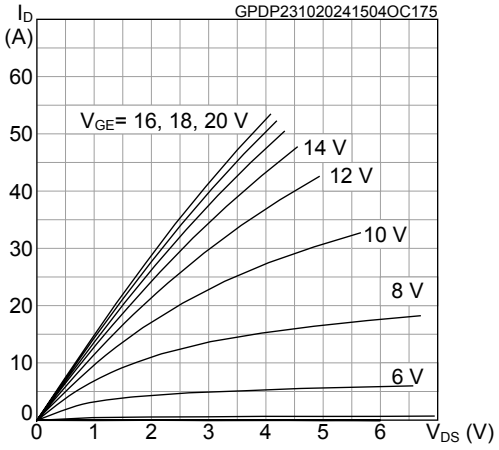


Figure 5. Typical transfer characteristics

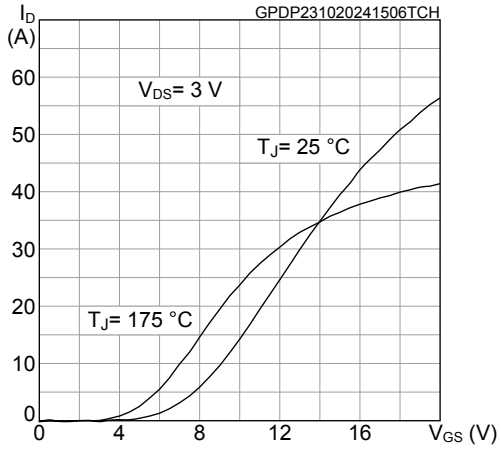


Figure 6. Total power dissipation

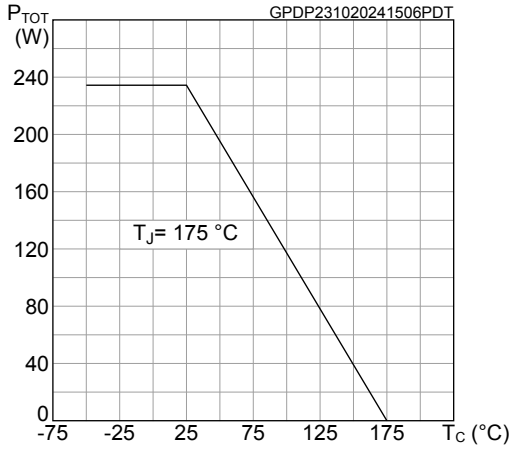


Figure 7. Maximum continuous drain current vs. case temperature

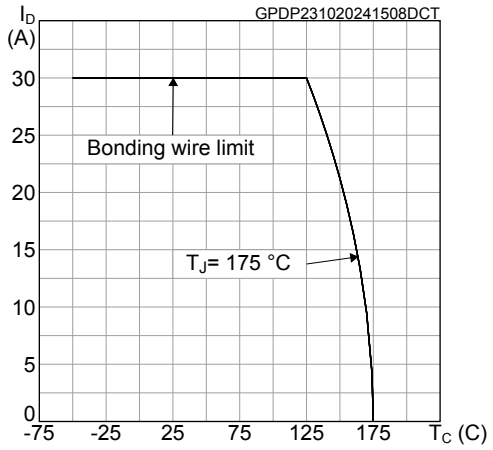


Figure 8. Typical gate charge characteristics

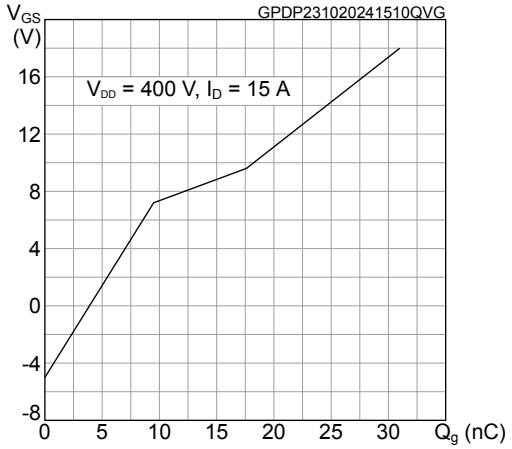


Figure 9. Typical capacitance characteristics

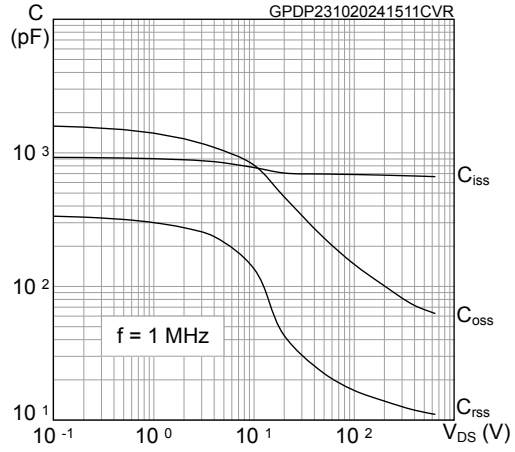


Figure 10. Normalized breakdown voltage vs temperature

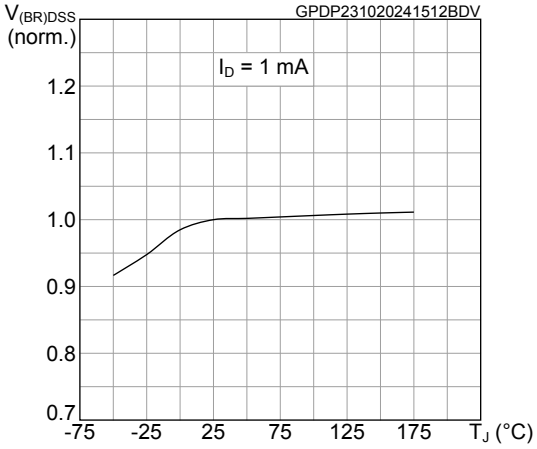


Figure 11. Normalized gate threshold vs temperature

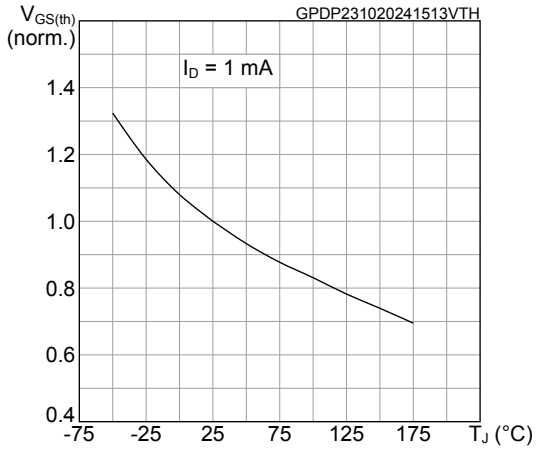


Figure 12. Normalized on-resistance vs temperature

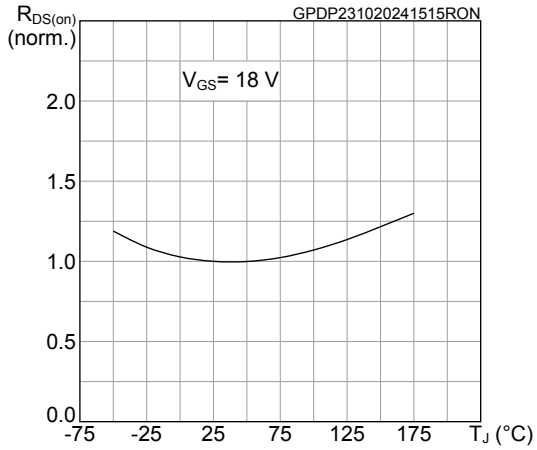


Figure 13. Typical reverse conduction characteristics (T_J = 25 °C)

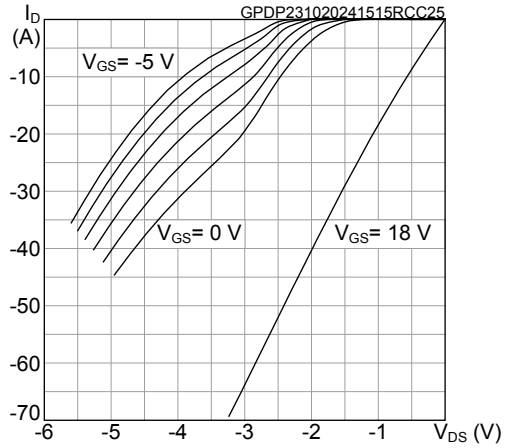


Figure 14. Typical reverse conduction characteristics (T_J = 175 °C)

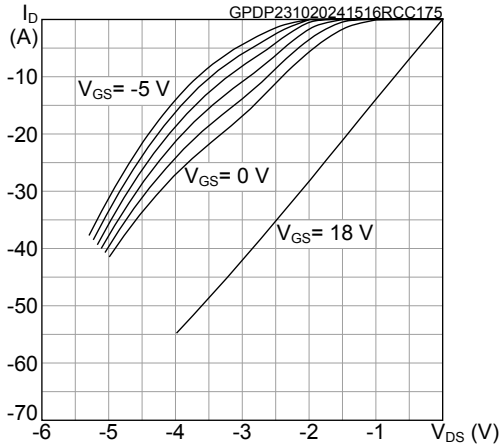


Figure 15. Typical switching energy vs drain current

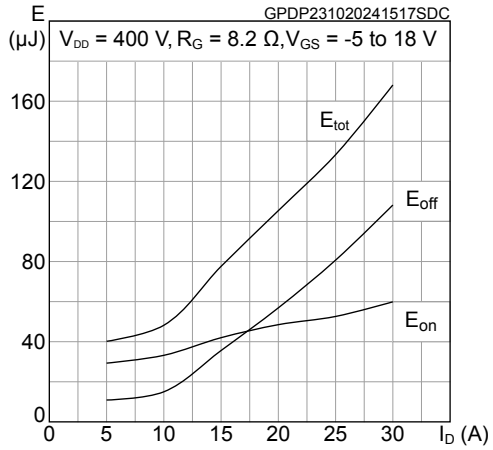


Figure 16. Typical switching energy vs supply voltage

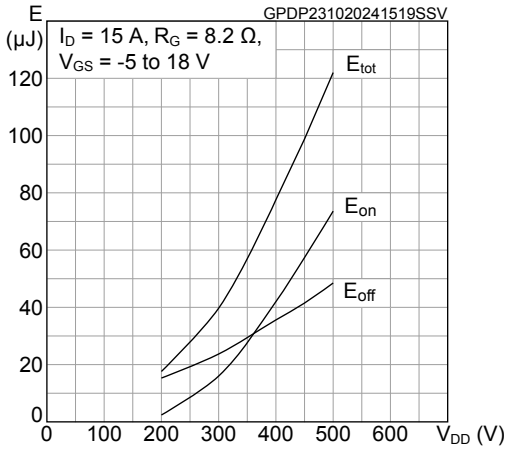
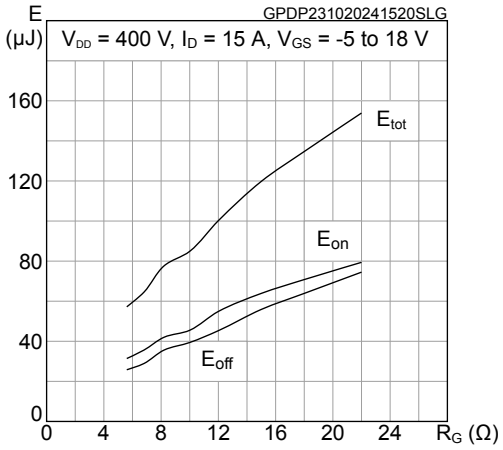


Figure 17. Typical switching energy vs gate resistance

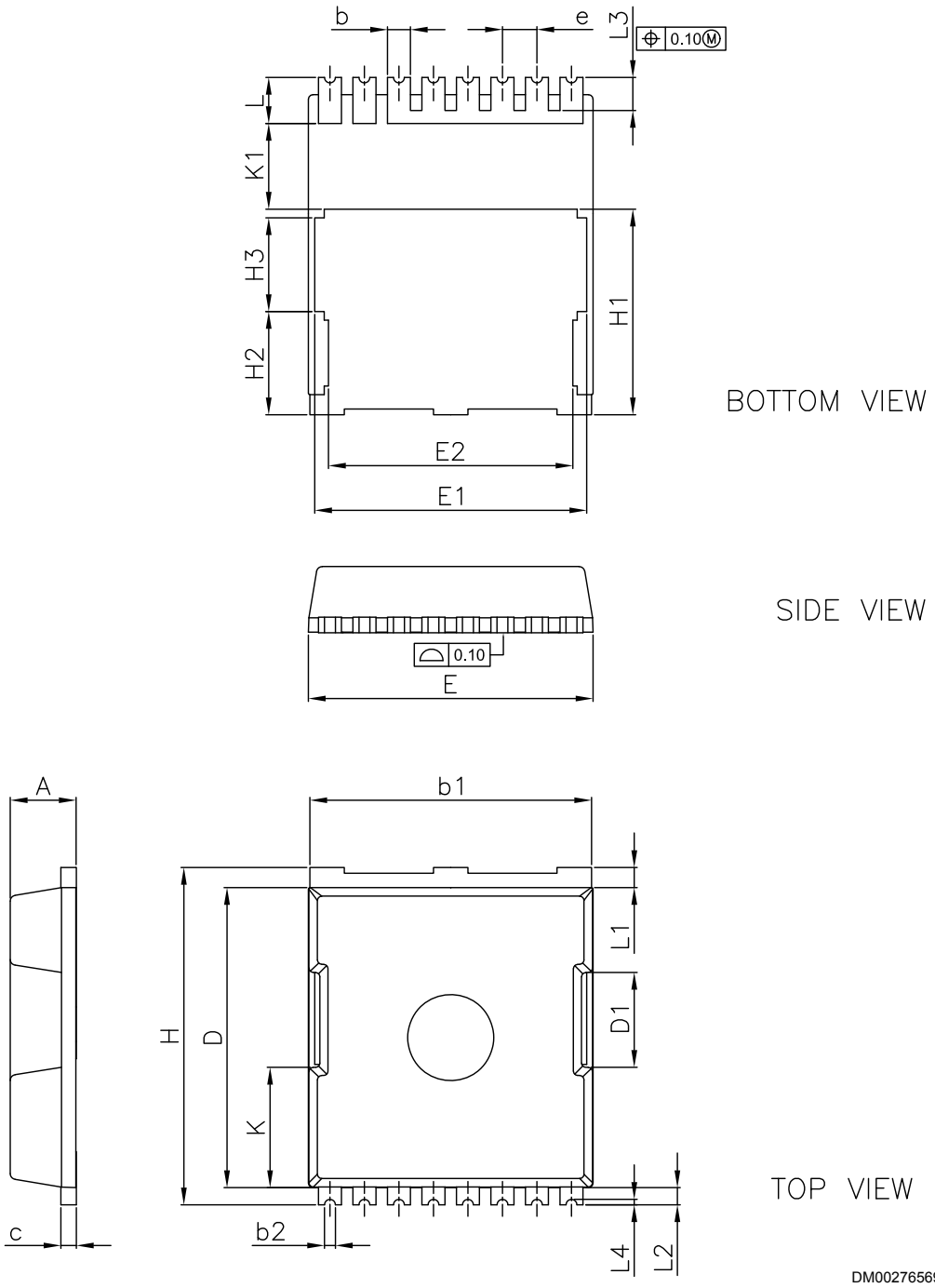


3 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 TO-LL package information

Figure 18. TO-LL package outline

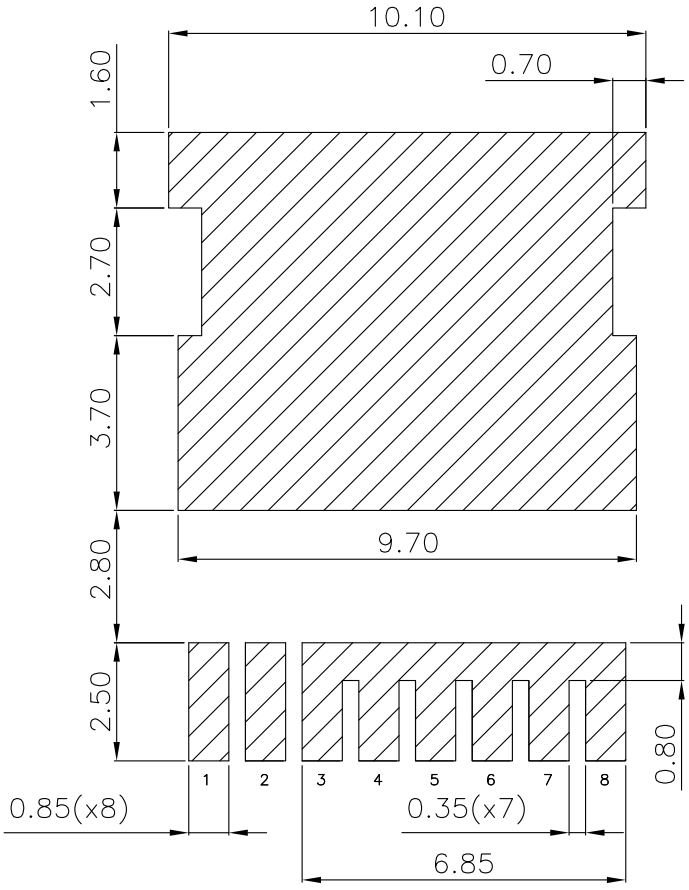


DM00276569_SiC_Rev_7

Table 8. **TO-LL package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.40
b	0.60	0.80	0.90
b1	9.70	9.80	9.90
b2	0.20		0.50
c	0.40	0.50	0.60
D	10.28	10.43	10.58
D1	3.15	3.30	3.45
E	9.70	9.90	10.10
E1	9.31	9.46	9.61
E2	8.35	8.50	8.65
e	1.10	1.20	1.30
H	11.48	11.73	11.88
H1	7.00	7.15	7.30
H2	3.34	3.59	3.84
H3	3.11	3.26	3.41
K	4.03	4.18	4.33
K1	2.70		
L	1.45	1.60	1.75
L1	0.55	0.70	0.85
L2	0.45	0.60	0.75
L3	1.00	1.15	1.30
L4	0.05		0.40

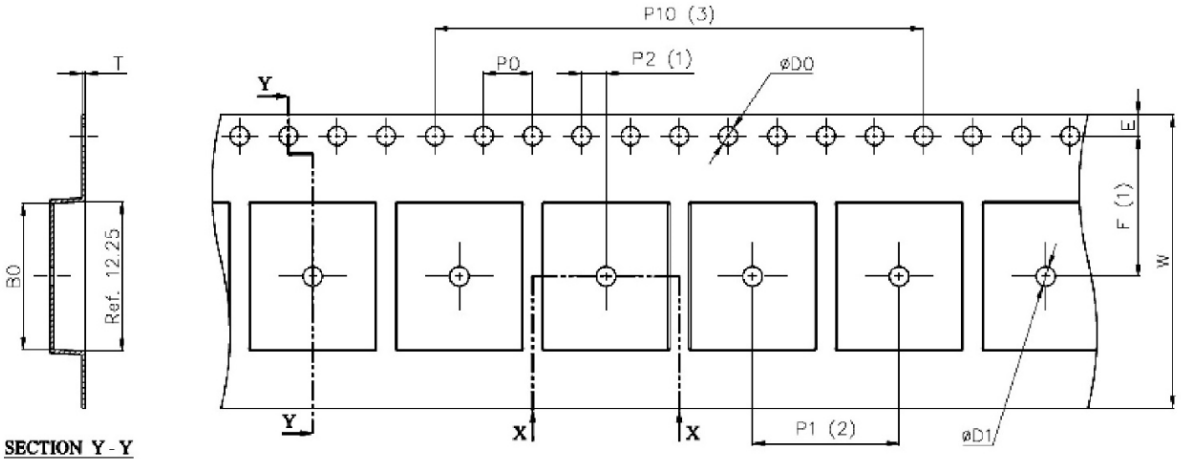
Figure 19. **TO-LL recommended footprint (dimensions are in mm)**



DM00276569_7_SiC_FP

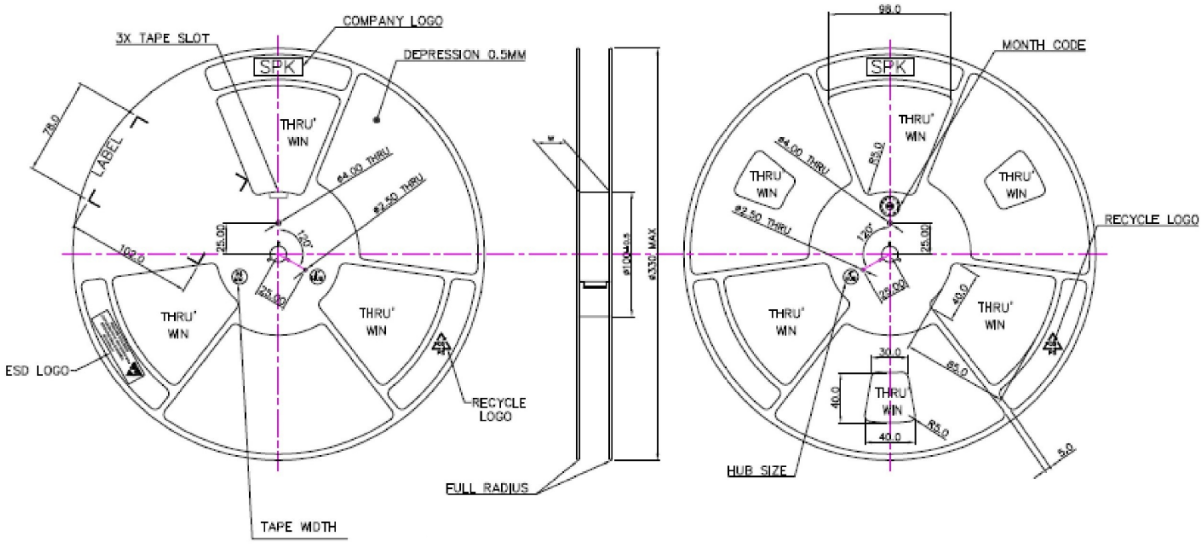
3.2 TO-LL packing information

Figure 20. **Carrier tape outline and dimensions**



Dimension List			
Annote	Millmeter	Annote	Millmeter
A0	10.20±0.10	P2	2.00±0.10
B0	11.98±0.10	P10	40.00±0.20
K0	2.60±0.10	E	1.75±0.10
D0	1.50$^{+0.10}_{-0}$	F	11.50±0.10
D1	1.60±0.10	W	24.00±0.30
P0	4.00±0.10	T	0.30±0.05
P1	12.00±0.10		

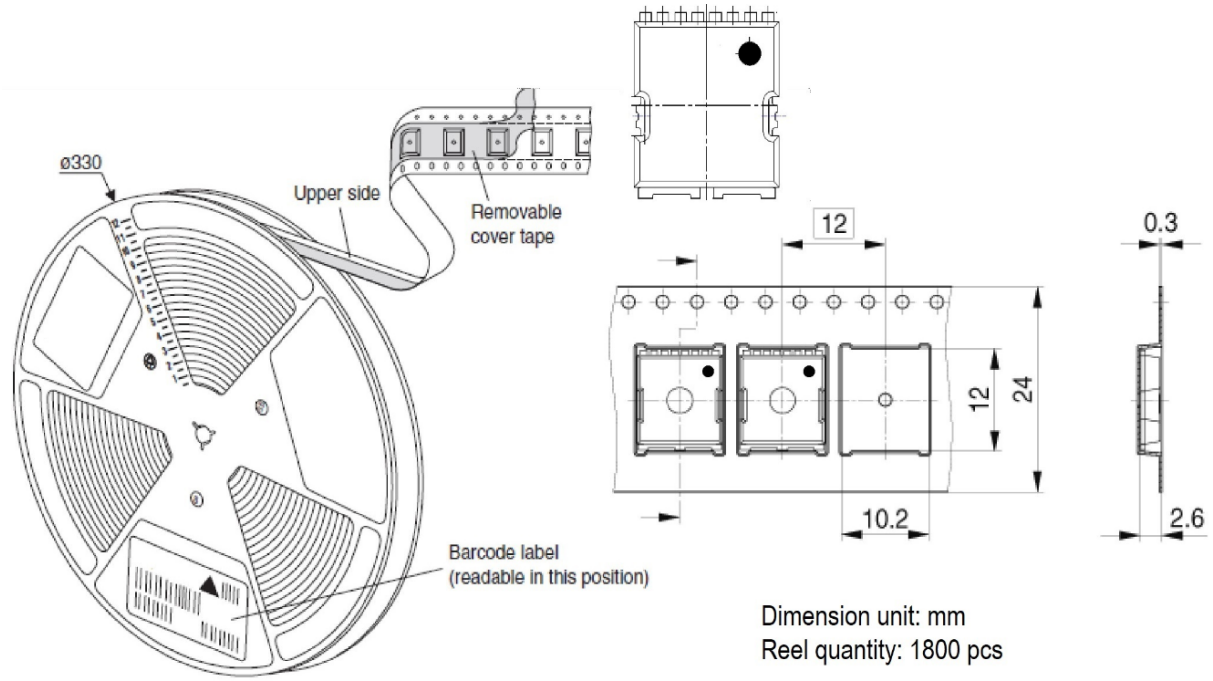
Figure 21. **Reel outline and dimensions**



SPECIFICATION							
TAPE WIDTH	W	U	X	V	Y	Z	P
24mm	24.4	1.50	24.5	20.0	0.55	6.00	2

Dimension unit: mm

Figure 22. **TO-LL orientation in tape pocket**



Revision history

Table 9. **Document revision history**

Date	Revision	Changes
29-Oct-2024	1	First release.

Contents